Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor element comprising:

a layer comprising titanium formed over a substrate;

a gate electrode layer formed over the layer;

a gate insulating film formed [[over]] in contact with the gate electrode layer;

a semiconductor film formed over the gate insulating film;

a pair of n-type impurity regions formed over the semiconductor film;

an insulating film that is interposed between the pair of n-type impurity regions and that is formed over the semiconductor film; and

a conductive layer formed over the pair of n-type impurity regions,

wherein the layer comprising titanium is wider than the gate electrode layer.

2. (Currently Amended) A semiconductor element comprising:

a layer comprising titanium formed over a substrate;

a gate electrode layer formed over the layer;

a gate insulating film formed [[over]] in contact with the gate electrode layer;

a semiconductor film formed over the gate insulating film;

a pair of n-type impurity regions formed over the semiconductor film;

an insulating film having a thickness of 100 nm or more that is interposed between the pair of n-type impurity regions and that is formed over the semiconductor film; and

a conductive layer formed over the pair of n-type impurity regions,

wherein the layer comprising titanium is wider than the gate electrode layer.

3. (Currently Amended) A semiconductor element comprising:

a layer comprising titanium formed over a substrate;

a gate electrode layer formed over the layer;

a gate insulating film formed [[over]] in contact with the gate electrode layer;

a semiconductor film formed over the gate insulating film;

a pair of n-type impurity regions formed over the semiconductor film;

an insulating film that is interposed between the pair of n-type impurity regions and that is formed over the semiconductor film; and

a conductive layer formed over the pair of n-type impurity regions;

wherein a thickness of a portion of the semiconductor film over which the insulating film is formed is thinner than that of the other semiconductor film, and the semiconductor film over which the insulating film is formed has a thickness of 10 nm or more, and

wherein the layer comprising titanium is wider than the gate electrode layer.

4. (Original) A semiconductor element according to any one of claims 1 to 3, wherein the insulating film comprises at least one selected from the group consisting of polyimide, acrylic, and a material which has a skeleton formed by a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as a substituent.

5. (Original) A semiconductor element according to any one of claims 1 to 3, wherein the layer comprises titanium oxide.

6. (Original) A semiconductor element according to any one of claims 1 to 3, wherein the semiconductor element is incorporated in at least one selected from the group consisting of a TV reception set, an electronic book and a cellular phone.

7-12. (Canceled)

13. (Currently Amended) A liquid crystal display device comprising:

a layer comprising titanium formed over a substrate;

a gate electrode layer formed over the layer;

a gate insulating film formed [[over]] in contact with the gate electrode layer;

a semiconductor film formed over the gate insulating film;

a pair of n-type impurity regions formed over the semiconductor film;

an insulating film that is interposed between the pair of n-type impurity regions and that is formed over the semiconductor film;

a conductive layer formed over the pair of n-type impurity regions; and

a pixel electrode electrically connected to the conductive layer,

wherein the layer comprising titanium is wider than the gate electrode layer.

14. (Currently Amended) A liquid crystal display device comprising:

a layer comprising titanium formed over a substrate;

a gate electrode layer formed over the layer;

a gate insulating film formed [[over]] in contact with the gate electrode layer;

a semiconductor film formed over the gate insulating film;

a pair of n-type impurity regions formed over the semiconductor film;

an insulating film having a thickness of 100 nm or more that is interposed between the pair of n-type impurity regions and that is formed over the semiconductor film;

a conductive layer formed over the pair of n-type impurity regions; and

a pixel electrode electrically connected to the conductive layer,

wherein the layer comprising titanium is wider than the gate electrode layer.

15.(Currently Amended)A liquid crystal display device comprising:

a layer comprising titanium formed over a substrate;

a gate electrode layer formed over the layer;

a gate insulating film formed [[over]] in contact with the gate electrode layer;

a semiconductor film formed over the gate insulating film;

a pair of n-type impurity regions formed over the semiconductor film;

an insulating film that is interposed between the pair of n-type impurity regions and that is formed over the semiconductor film;

a conductive layer formed over the pair of n-type impurity regions; and

a pixel electrode electrically connected to the conductive layer;

wherein a thickness of a portion of the semiconductor film over which the insulating film is formed is thinner than that of the other semiconductor film, and the semiconductor film over which the insulating film is formed has a thickness of 10 nm or more, and

wherein the layer comprising titanium is wider than the gate electrode layer.

16. (Original) A liquid crystal display device according to any one of claims 13 to 15, wherein the insulating film comprises at least one selected from the group consisting of polyimide, acrylic, and a material which has a skeleton formed by a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as a substituent.

17. (Original) A liquid crystal display device according to any one of claims 13 to 15, wherein the layer comprises titanium oxide.

18. (Original) A liquid crystal display device according to any one of claims 13 to 15, wherein the liquid crystal display device is incorporated in at least one selected from the group consisting of a TV reception set, an electronic book and a cellular phone.

19-24.(Canceled)